

What is claimed is:

1. An LSI device comprising:

an SOI substrate having a SOI layer including a core region  
to which a first driving voltage is applied and an interface  
5 region to which a second driving voltage higher than the first  
driving voltage is applied;

a device separation region for separating the SOI layer  
into the core region and the interface region, wherein a  
thickness of the SOI layer of the core region is thinner than  
10 a thickness of the SOI layer of the interface region,

a plurality of first MOSFETs formed in the core region  
and in which the SOI layer of the above core region is a fully  
depleted Si channel; and

a plurality of second MOSFETs formed in the interface  
15 region and in which the SOI layer of the above interface region  
is a fully depleted Si channel.

2. The LSI device according to claim 1, wherein a channel  
length of the first MOSFET formed in the core region is made  
shorter than a channel length of the second MOSFET formed in  
20 the interface region.

3. The LSI device according to claim 1, wherein a  
thickness of the SOI layer of the above core region is 30 nm  
or less.

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